

650V 10A N-Channel Enhancement Mode Power MOSFET

Description

The AKT10N65T is an N-Channel enhancement mode power MOSFET which using proprietary planar stripe and DMOS technology.

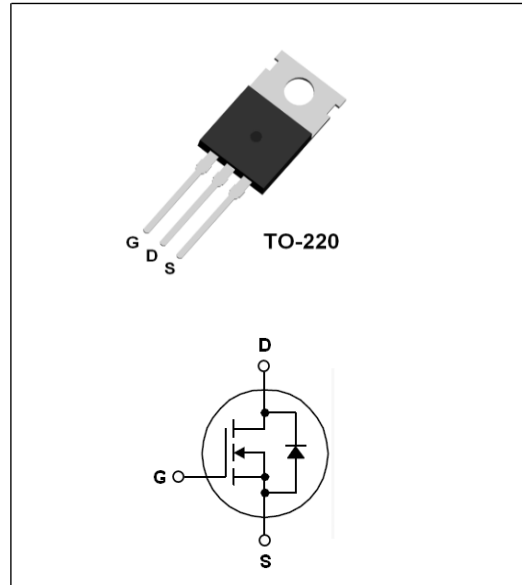
This MOSFET has low static on-resistance and high avalanche energy strength. This device provide excellent switching performance for UPS,DC-DC converters and AC-DC power supply.

Features

- Low on-Resistance: $R_{DS(on)}=0.85\Omega(\text{typ.})$
- Special Process Technology for high ESD Capability
- 100% Avalanche Test
- Good Stability and Uniformity with High E_{AS}

Applications

- UPS Applications
- DC-DC Converters and AC-DC Power Supply



Absolute Maximum Ratings @ $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Unit
V_{DSS}	Drain to Source Voltage	650	V
V_{GSS}	Gate to Source Voltage	± 30	V
I_D	Drain Current	$T_C=25^\circ\text{C}$	10
		$T_C=100^\circ\text{C}$	6.5
I_{DM}	Pulsed Drain Current (Note1)	38	A
P_D	Maximum Power Dissipation	$T_C=25^\circ\text{C}$	156
	Derate above 25°C		2.22
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	490	mJ
T_J	Operating Junction Temperature Range	-55~+150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55~+150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Ratings	Unit
$R_{th(J-C)}$	Thermal Resistance, Junction to case	0.83	$^\circ\text{C}/\text{W}$
$R_{th(J-A)}$	Thermal Resistance, Junction to Ambient	62.5	$^\circ\text{C}/\text{W}$

Electrical Characteristics @ $T_C=25\text{ }^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain to Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	650	-	-	V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2.0	-	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS}=10V, I_D=5A$	-	0.85	0.9	Ω
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=650V, V_{GS}=0V$	-	-	1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS}=\pm 30V, V_{DS}=0V$	-	-	± 100	nA

D-S Diode Characteristics and Maximum Rating @ $T_C=25\text{ }^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Maximum Drain to Source Diode Forward Current		-	-	10	A
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS}=0V, I_S=10A$	-	0.88	1	V
t_{rr}	Reverse Recovery Time	$V_{GS}=0V, I_S=10A,$	-	575	-	ns
Q_{rr}	Reverse Recovery Charge	$di/dt=-100A/\mu s$	-	4.6	-	μC

Switching Characteristics @ $T_C=25\text{ }^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$I_D=10A,$ $V_{DD}=325V,$ $R_G=25\Omega$ (Note 3)	-	41	-	ns
t_r	Rising Time		-	75	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	55	-	ns
t_f	Falling Time		-	36	-	ns
C_{iss}	Input Capacitance	$V_{GS}=0V, V_{DS}=25V,$ $f=1.0MHz$	-	1200	-	pF
C_{oss}	Output Capacitance		-	165	-	pF
C_{rss}	Reverse Transfer Capacitance		-	8	-	pF
Q_g	Total Gate Charge	$I_D=10A,$ $V_{DS}=520V$ $V_{GS}=10V$ (Note 3)	-	25	-	nC
Q_{gs}	Gate to Source Charge		-	7.7	-	nC
Q_{gd}	Gate to Drain Charge		-	6.9	-	nC

Note:

1. Repetitive rating: pulse-width limited by maximum junction temperature
2. $L=2mH, V_{DD}=100V, V_G=10V, @T_C=25\text{ }^\circ\text{C}$
3. Essentially independent of operating temperature typical characteristics

Typical Performance Characteristics

Fig. 1. Typical on-Region Characteristics

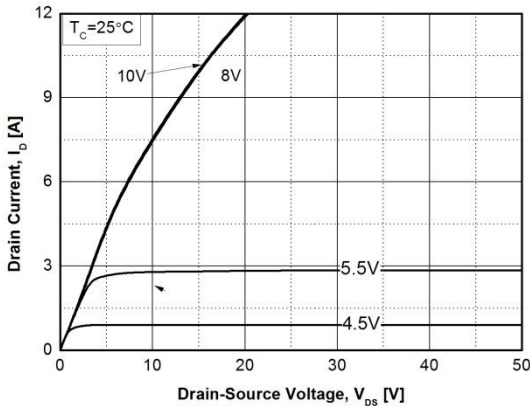


Fig. 2. Typical Transfer Characteristics

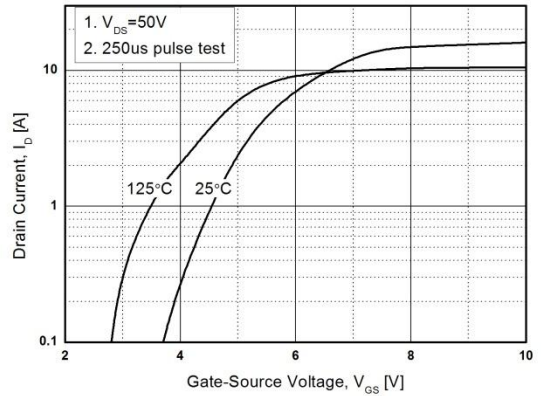


Fig. 3. Static on-Resistance vs. I_D

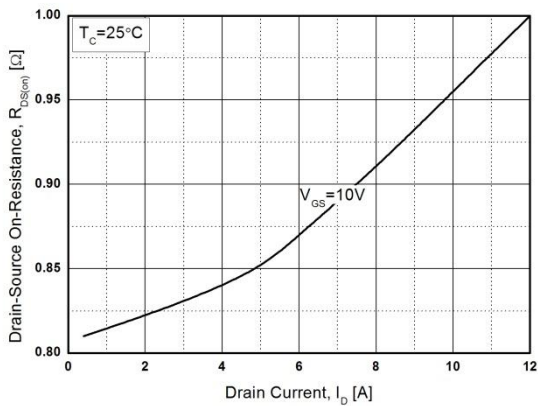


Fig. 4. Body Diode Forward Voltage vs. I_{DR}

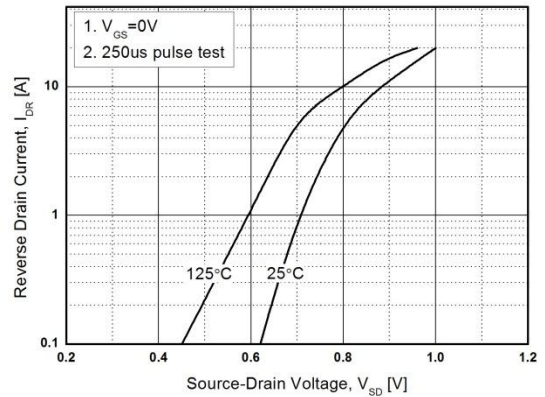


Fig. 5. Capacitance Characteristics

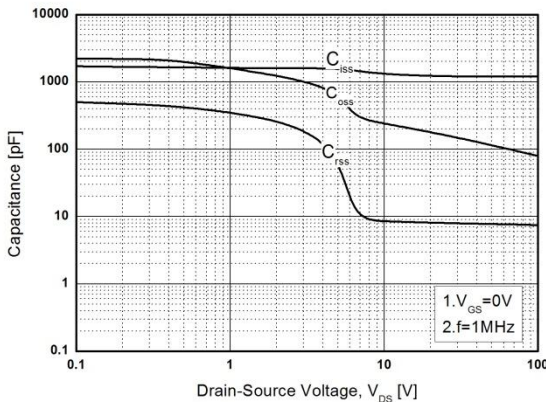
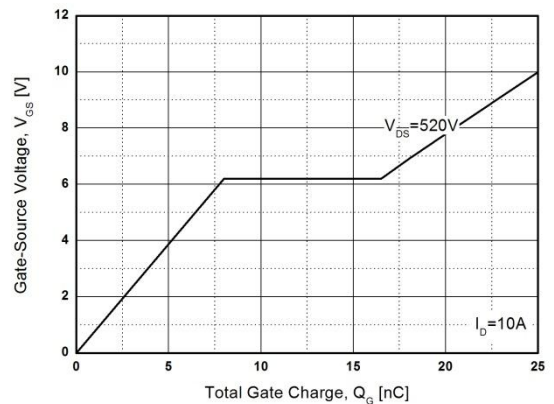


Fig. 6. Gate Charge Characteristics



Typical Performance Characteristics

Fig. 7. Breakdown Voltage vs. Temperature

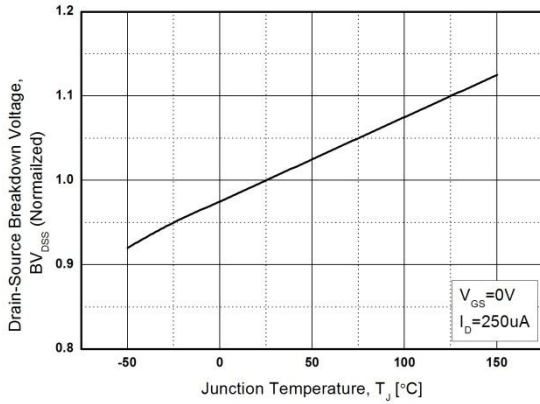


Fig. 8. Static on-Resistance vs. Temperature

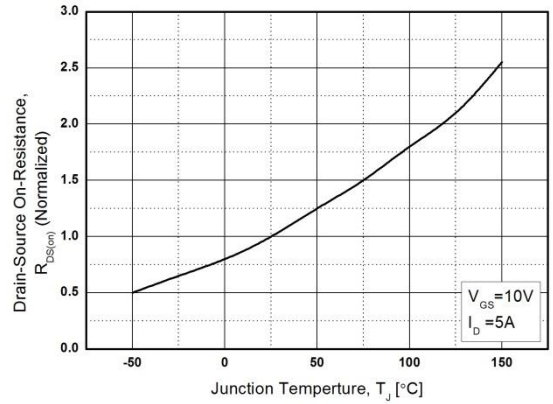


Fig. 9. Maximum Safe Operating Area

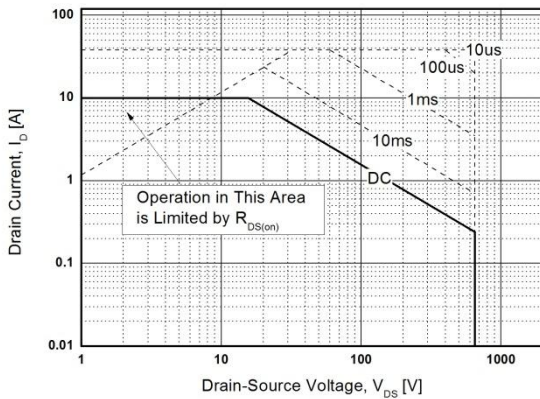


Fig. 10. Maximum Drain Current vs. Temperature

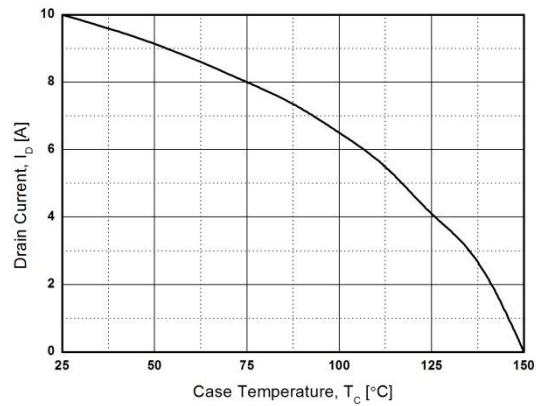
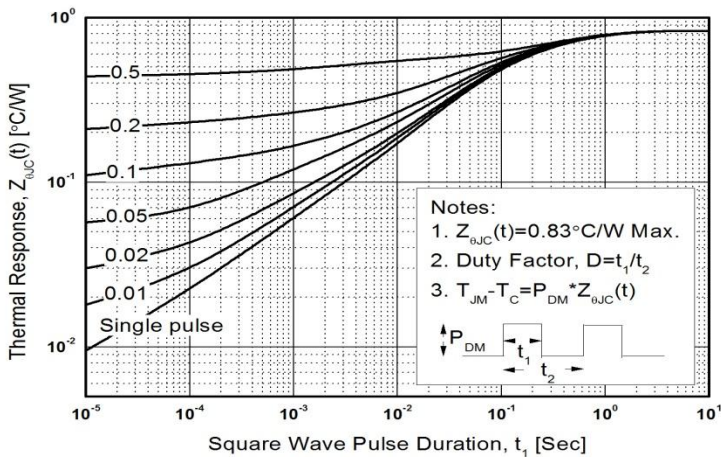


Fig. 11. Transient Thermal Response Curve



Package Dimensions

TO-220

(Dimensions in Millimeters)

